

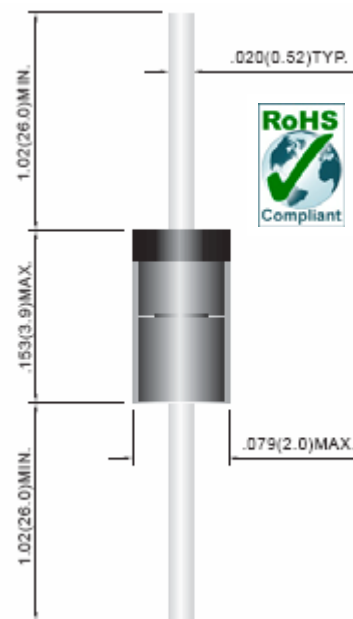
Zener Diodes

Features

- 500mW Power Dissipation
- High Stability
- Zener Voltage from 3.3V to 39V
- High temperature soldering guaranteed 265°C/10 seconds
/.037" (9.5mm) lead length,
- RoHS compliant

Mechanical Data

Case:	DO-35, Molded Glass
Terminals:	Axial leads, solderable per MIL-STD-202, Method 208
Weight:	0.125 gram



Dimensions in inch (mm)

Maximum Ratings & Electrical Characteristics

($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Value	Unit	Conditions
PD	Power Dissipation above 25° C	500	mW	
VF	Forward Voltage	1.5	V	IF= 0.1 A
TJ	Max. Junction Temperature	175	° C	
TSTG	Storage Temperature Range	-65 to +175	° C	

1N4678~1N4717

P/N	Normal Zener Voltage			Max Voltage Change	Max Zener Current	Max Reverse Current	
	VZ @ IZT=50μA			ΔVZ (V) note1		IR @ VR	
	Nom. V	Min. V	Max. V		mA	μA	VR
1N4678	1.8	1.71	1.89	0.70	120	7.5	1
1N4679	2	1.9	2.1	0.70	110	5	1
1N4680	2.2	2.09	2.31	0.75	100	4	1
1N4681	2.4	2.28	2.52	0.80	95	2	1
1N4682	2.7	2.565	2.835	0.85	90	1	1
1N4683	3	2.85	3.15	0.90	85	0.8	1
1N4684	3.3	3.135	3.465	0.95	80	7.5	1.5
1N4685	3.6	3.42	3.78	0.95	75	7.5	2
1N4686	3.9	3.705	4.095	0.97	70	5	2
1N4687	4.3	4.085	4.515	0.99	65	4	2
1N4688	4.7	4.465	4.935	0.99	60	10	3
1N4689	5.1	4.845	5.355	0.97	55	10	3
1N4690	5.6	5.32	5.88	0.96	50	10	4
1N4691	6.2	5.89	6.51	0.95	45	10	5
1N4692	6.8	6.46	7.14	0.90	35	10	5.1
1N4693	7.5	7.125	7.875	0.75	31.8	10	5.7
1N4694	8.2	7.79	8.61	0.5	29	1	6.2
1N4695	8.7	8.265	9.135	0.1	27.4	1	6.6
1N4696	9.1	8.645	9.555	0.08	26.2	1	6.9
1N4697	10	9.5	10.5	0.1	24.8	1	7.6
1N4698	11	10.45	11.55	0.11	21.6	0.05	8.4
1N4699	12	11.4	12.6	0.12	20.4	0.05	9.1
1N4700	13	12.35	13.65	0.13	19	0.05	9.8
1N4701	14	13.3	14.7	0.14	17.5	0.05	10.6
1N4702	15	14.25	15.75	0.15	16.3	0.05	11.4
1N4703	16	15.2	16.8	0.16	15.4	0.05	12.1
1N4704	17	16.15	17.85	0.17	14.5	0.05	12.9
1N4705	18	17.1	18.9	0.18	13.2	0.05	13.6
1N4706	19	18.05	19.95	0.19	12.5	0.05	14.4

1N4678~1N4717

P/N	Normal Zener Voltage			Max Voltage Change	Max Zener Current	Max Reverse Current	
	VZ @ IZT=50μA			ΔVZ (V) note1		IR @ VR	
	Nom. V	Min. V	Max. V		mA	μA	VR
1N4707	20	19	21	0.2	11.9	0.01	15.2
1N4708	22	20.9	23.1	0.22	10.8	0.01	16.7
1N4709	24	22.8	25.2	0.24	9.9	0.01	18.2
1N4710	25	23.75	26.25	0.25	9.5	0.01	19
1N4711	27	25.65	28.35	0.27	8.8	0.01	20.4
1N4712	28	26.6	29.4	0.28	8.5	0.01	21.2
1N4713	30	28.5	31.5	0.3	7.9	0.01	22.8
1N4714	33	31.35	34.65	0.33	7.2	0.01	25
1N4715	36	34.2	37.8	0.36	6.6	0.01	27.3
1N4716	39	37.05	40.95	0.39	6.1	0.01	29.6
1N4717	43	40.85	45.15	0.43	5.5	0.01	32.6

Note1. ΔVz (V) is the difference between Vz at 100mA and at 10mA

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